

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

TPHR8504PL

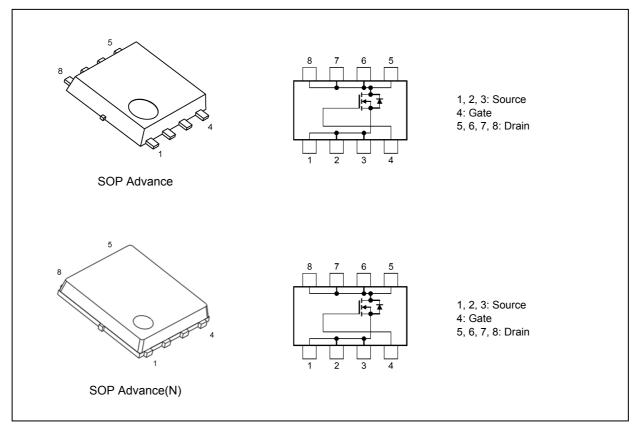
1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 23 \text{ nC (typ.)}$
- (3) Small output charge: $Q_{oss} = 85.4 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance: $R_{DS(ON)} = 0.7 \text{ m}\Omega$ (typ.) ($V_{GS} = 10 \text{ V}$)
- (5) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 40 \text{ V)}$
- (6) Enhancement mode: $V_{th} = 1.4 \text{ to } 2.4 \text{ V } (V_{DS} = 10 \text{ V}, I_D = 1.0 \text{ mA})$

3. Packaging and Internal Circuit



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Start of commercial production



4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

| Characteris | tics | | Symbol | Rating | Unit |
|--------------------------------|--------------------------|--------------------|------------------|------------|------|
| Drain-source voltage | | | V_{DSS} | 40 | V |
| Gate-source voltage | | | V_{GSS} | ±20 | |
| Drain current (DC) | (T _c = 25 °C) | (Note 1), (Note 2) | I _D | 150 | Α |
| Drain current (DC) | (Silicon limit) | (Note 1), (Note 2) | I _D | 340 | Α |
| Drain current (pulsed) | (t = 100 μs) | (Note 1) | I _{DP} | 500 | Α |
| Power dissipation | (T _c = 25 °C) | | P _D | 170 | W |
| Power dissipation | | (Note 3) | P _D | 3.0 | W |
| Power dissipation | | (Note 4) | P_{D} | 1.0 | W |
| Single-pulse avalanche energy | · | (Note 5) | E _{AS} | 336 | mJ |
| Single-pulse avalanche current | | (Note 5) | I _{AS} | 120 | Α |
| Channel temperature | | | T _{ch} | 175 | ů |
| Storage temperature | - | | T _{stg} | -55 to 175 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit | | |
|---------------------------------------|--------------------------|----------|-----------------------|------|------|
| Channel-to-case thermal resistance | (T _c = 25 °C) | | R _{th(ch-c)} | 0.88 | °C/W |
| Channel-to-ambient thermal resistance | (T _a = 25 °C) | (Note 3) | R _{th(ch-a)} | 50 | |
| Channel-to-ambient thermal resistance | (T _a = 25 °C) | (Note 4) | R _{th(ch-a)} | 142 | |

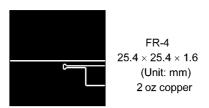
Note 1: Ensure that the channel temperature does not exceed 175 °C.

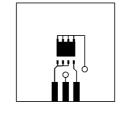
Note 2: Limited by package limit. Silicon chip capability is 340 A. ($T_c = 25$ °C)

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 32 V, T_{ch} = 25 °C (initial), L = 18 μ H, I_{AS} = 120 A





FR-4 $25.4 \times 25.4 \times 1.6$ (Unit: mm) 2 oz copper

Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a)

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±0.1 | μА |
| Drain cut-off current | I _{DSS} | V _{DS} = 40 V, V _{GS} = 0 V | _ | _ | 10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 40 | _ | | V |
| | V _{(BR)DSX} | $I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$ | 25 | _ | | |
| Gate threshold voltage | V_{th} | V _{DS} = 10 V, I _D = 1.0 mA | 1.4 | _ | 2.4 | |
| Drain-source on-resistance | R _{DS(ON)} | $V_{GS} = 4.5 \text{ V}, I_D = 50 \text{ A}$ | _ | 1.0 | 1.4 | mΩ |
| | | V _{GS} = 10 V, I _D = 50 A | _ | 0.7 | 0.85 | |

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|--|-----|------|------|------|
| Input capacitance | C _{iss} | V _{DS} = 20 V, V _{GS} = 0 V, f = 1 MHz | _ | 7370 | 9600 | pF |
| Reverse transfer capacitance | C _{rss} | | _ | 58 | _ | |
| Output capacitance | C _{oss} | | _ | 1930 | _ | |
| Gate resistance | r _g | _ | _ | 0.6 | 1.1 | Ω |
| Switching time (rise time) | t _r | See Fig. 6.2.1 | _ | 13 | _ | ns |
| Switching time (turn-on time) | t _{on} | | _ | 26 | _ | |
| Switching time (fall time) | t _f | | _ | 14 | _ | |
| Switching time (turn-off time) | t _{off} | | _ | 63 | _ | |

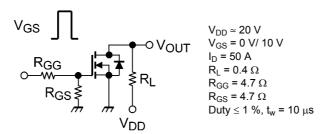


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------------|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus | Q_g | $V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$ | - | 103 | | nC |
| gate-drain) | | $V_{DD} \approx 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 50 \text{ A}$ | | 49 | | |
| Gate-source charge 1 | Q _{gs1} | $V_{DD} \approx 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 50 \text{ A}$ | | 25 | | |
| Gate-drain charge | Q_{gd} | | _ | 12.4 | _ | |
| Gate switch charge | Q_{SW} | | _ | 23 | _ | |
| Output charge | Q _{oss} | V _{DS} = 20 V, V _{GS} = 0 V | _ | 85.4 | _ | |



6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------------------------------|--|-----|------|------|------|
| Reverse drain current (pulsed) (Note 6) | I _{DRP} (t = 100 μs) | | 1 | ı | 500 | А |
| Diode forward voltage | V _{DSF} | I _{DR} = 150 A, V _{GS} = 0 V | _ | _ | -1.2 | V |
| Reverse recovery time1 | t _{rr1} | See Fig. 6.4.1 | | 49 | _ | ns |
| Reverse recovery charge1 | Q _{rr1} | | | 93 | _ | nC |

Note 6: Ensure that the channel temperature does not exceed 175 °C.

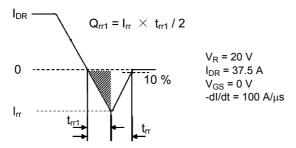
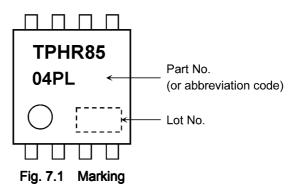


Fig. 6.4.1 t_{rr} Waveform

7. Marking





8. Characteristics Curves (Note)

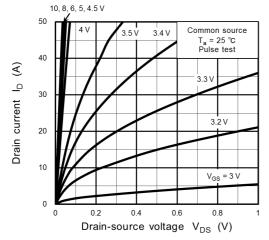


Fig. 8.1 I_D - V_{DS}

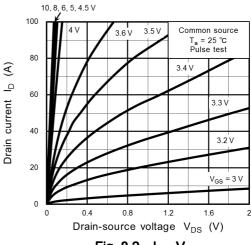


Fig. 8.2 I_D - V_{DS}

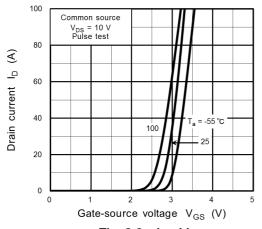


Fig. 8.3 I_D - V_{GS}

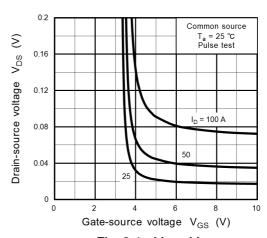


Fig. 8.4 V_{DS} - V_{GS}

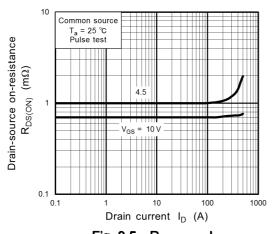


Fig. 8.5 R_{DS(ON)} - I_D

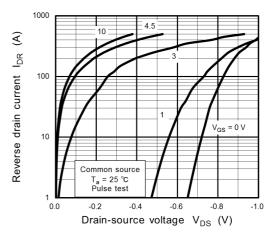


Fig. 8.6 I_{DR} - V_{DS}



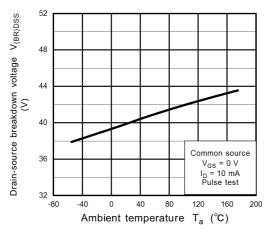
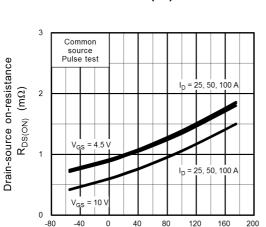


Fig. 8.7 V_{(BR)DSS} - T_a



Ambient temperature T_a (°C) **Fig. 8.9** $R_{DS(ON)}$ - T_a

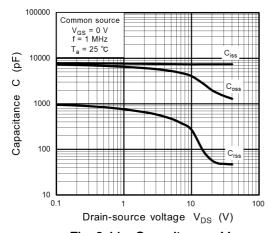


Fig. 8.11 Capacitance - V_{DS}

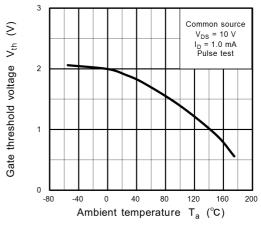


Fig. 8.8 V_{th} - T_a

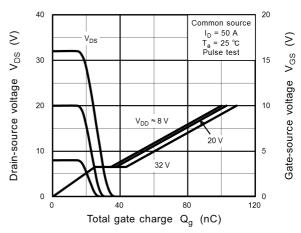


Fig. 8.10 Dynamic Input/Output Characteristics

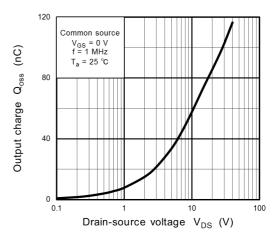


Fig. 8.12 Qoss - VDS



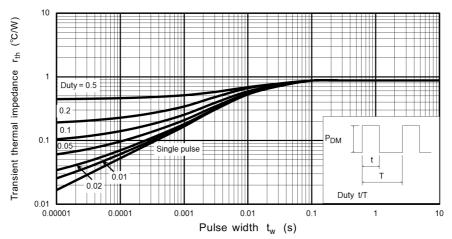


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

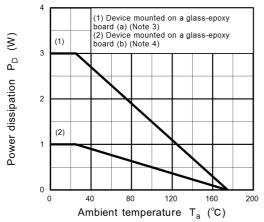


Fig. 8.14 P_D - T_a (Guaranteed Maximum)

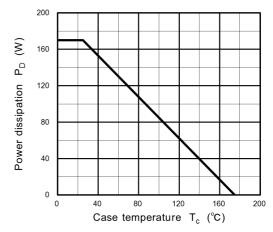


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

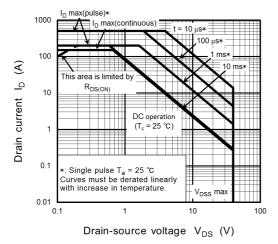


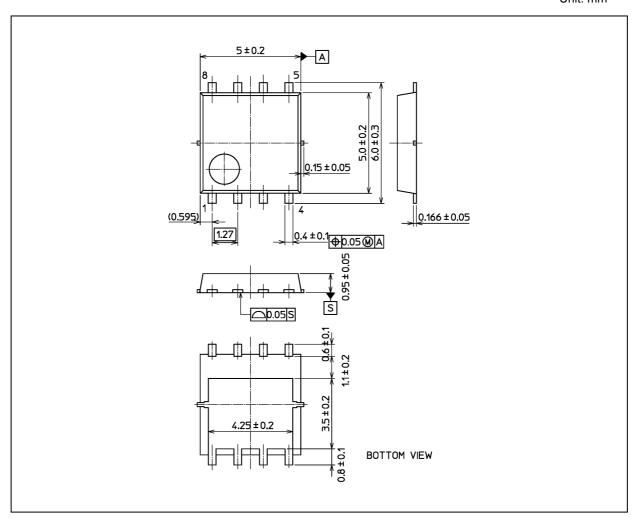
Fig. 8.16 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

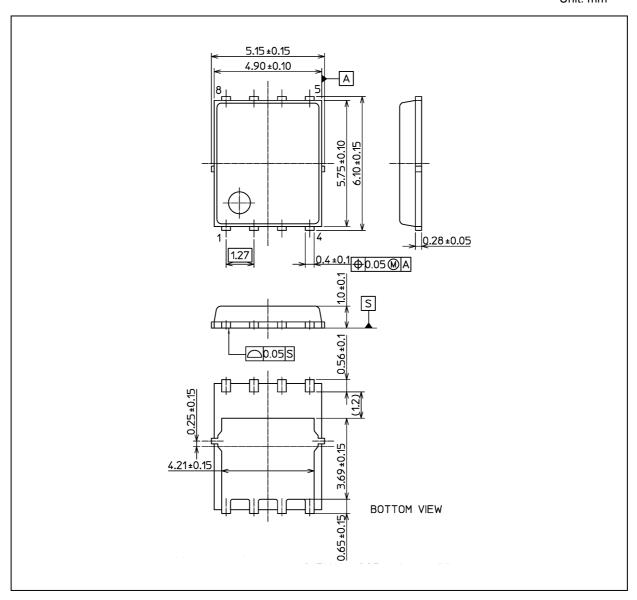
Weight: 0.087 g (typ.)

| ı | Package Name(s) |
|-----------------------|-----------------|
| TOSHIBA: 2-5Q1S | |
| Nickname: SOP Advance | |



Package Dimensions

Unit: mm



The package can be selected according to your preference. For details, please contact your TOSHIBA sales representative.

Weight: 0.111 g (typ.)

| Package Name(s) |
|--------------------------|
| TOSHIBA: 2-5W1A |
| Nickname: SOP Advance(N) |



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